SGIQ6Ö6D0;0 ṂṂŁ Q ǔ PRV ʃ ǫ̃ Ẓ ˥

N-Channel Enhancement Mode Field Effect Transistor in a PDFN3Ö3A-8L Plastic Package.

V_{DS} (V) = 30V

I_D =20 A (V_{GS} = 20V)

$R_{DS(ON)}$@10V 13mR(Typ.11mR)

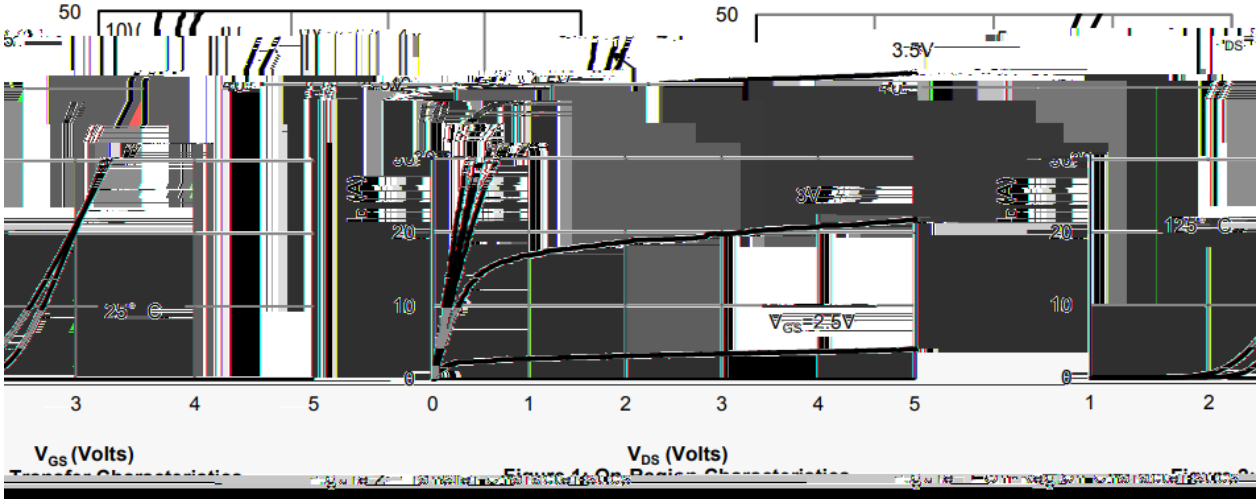
ㄅ ᵀ DHF0T434 ‰´ ㄨ ˈ ˎ ớ ɭ ∂ ı ŋ̀ ɾ ᵝ Qualified to AEC-Q101 Standards for High Reliability, HF Product.

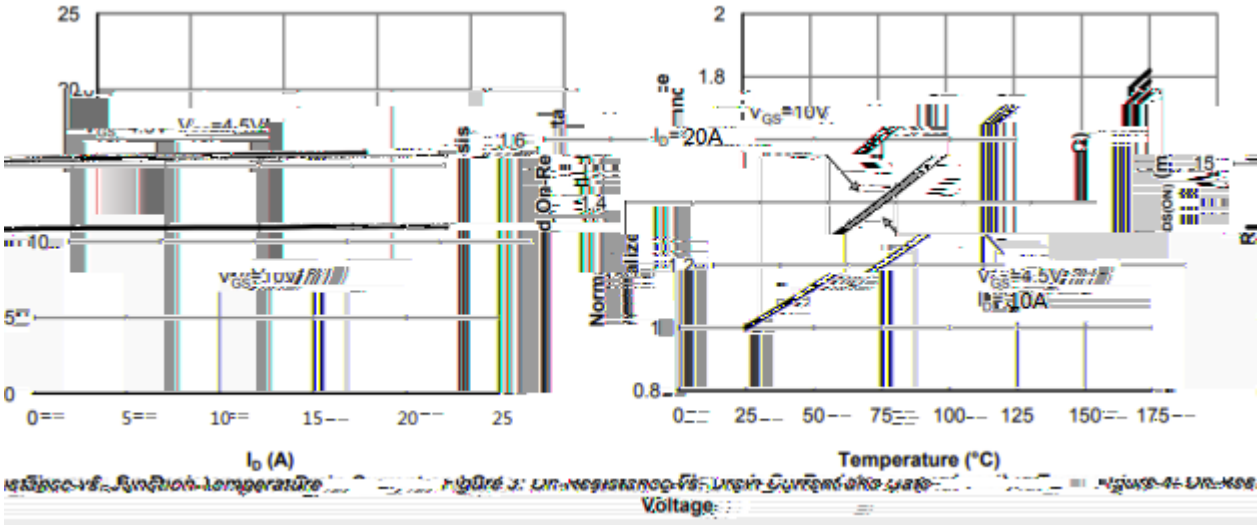
ʼ̂ ̂ ㄨ ı ˈ GF2GF ¯ ˝A ≡

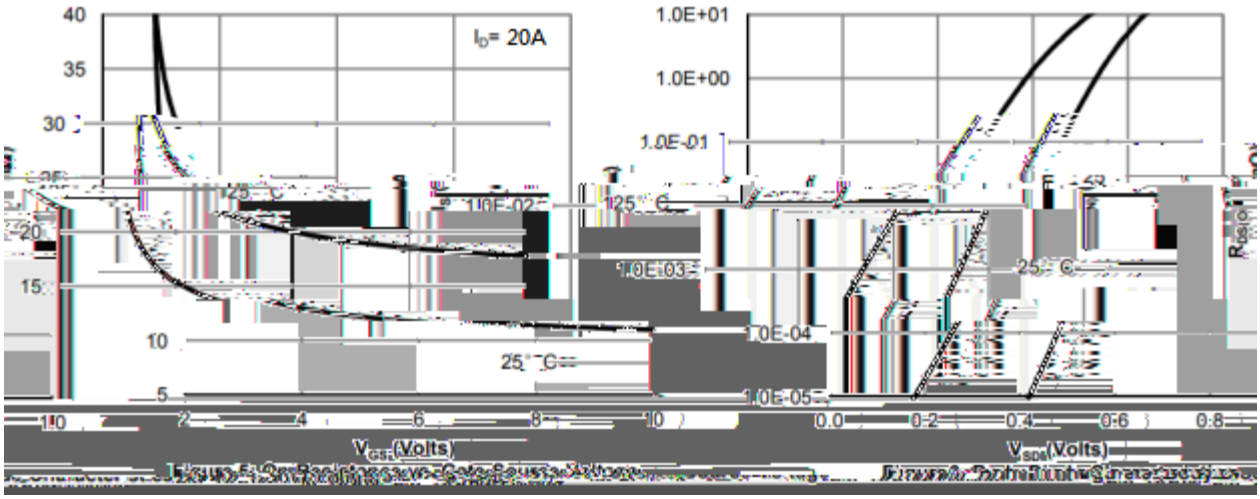
/ Absolute Maximum Ratings(Ta=25)

v ̈Ω̣ Parameter		ϟ N Symbol	̈Ω̣Ö Rating	D Ɉ Unit
Drain-Source Voltage		V_{DSS}	30	V
Drain Current		I_D(Tc=25)	20	A
Drain Current - Pulsed		I_{DM}	55	A
Gate-Source Voltage		V_{GSS}	±20	V
Single Pulsed Avalanche Energy		E_{AS}	199	mJ
Avalanche Current		I_{AS}	12.9	A
Power Dissipation		P_D(Tc=25)	15.5	W
Operating and Storage Temperature Range		T_J,T_{stg}	-55 to 150	
Junction-to-Ambient	t 10	$R_{\theta JA}$	30	/W
Junction-to-Ambient	Steady-State		60	
Junction-to-Case	Steady-State	$R_{\theta JC}$	8	

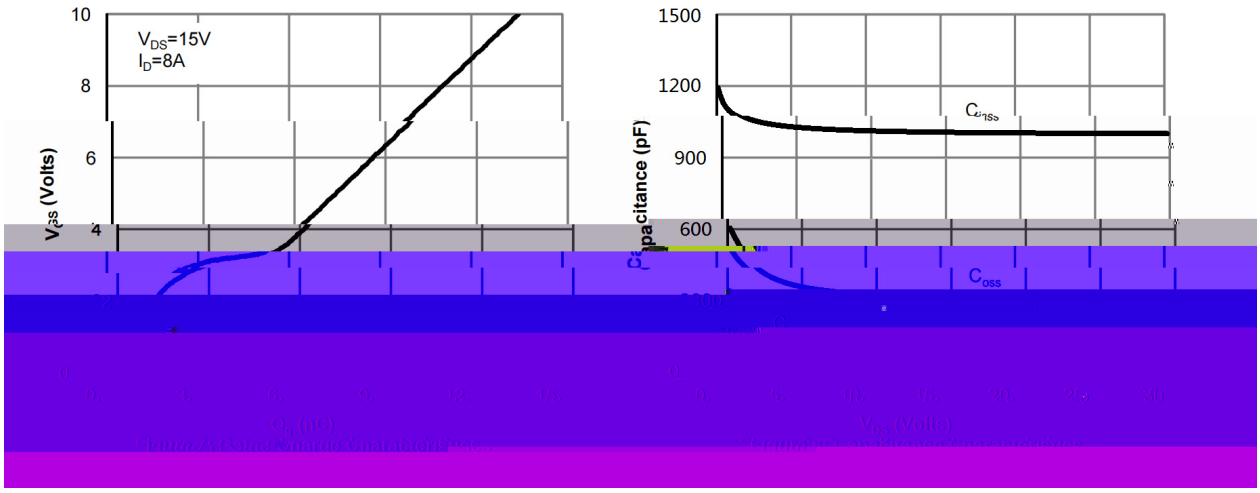
/ Electrical Characteristic Curve

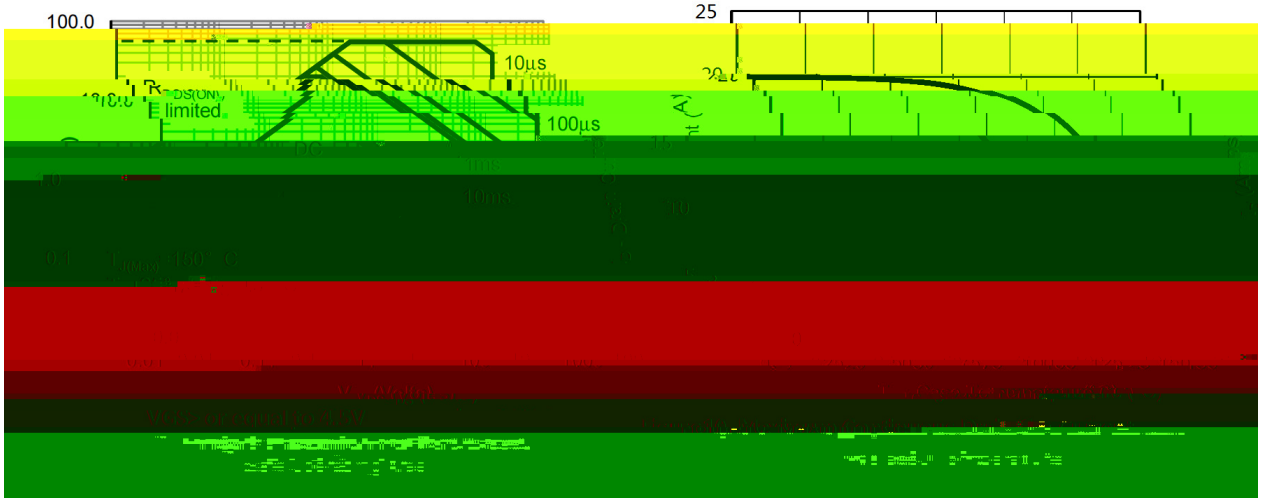


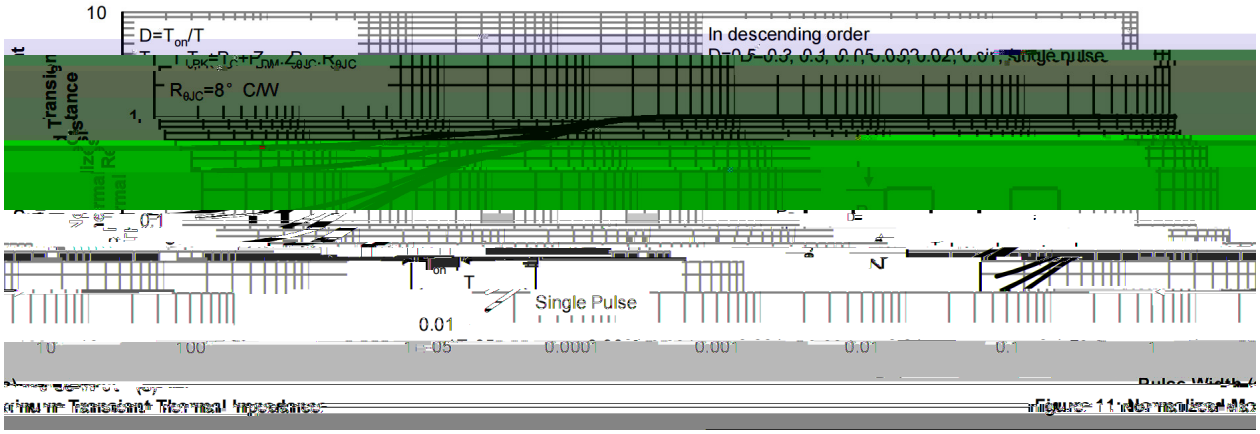




/ Electrical Characteristic Curve



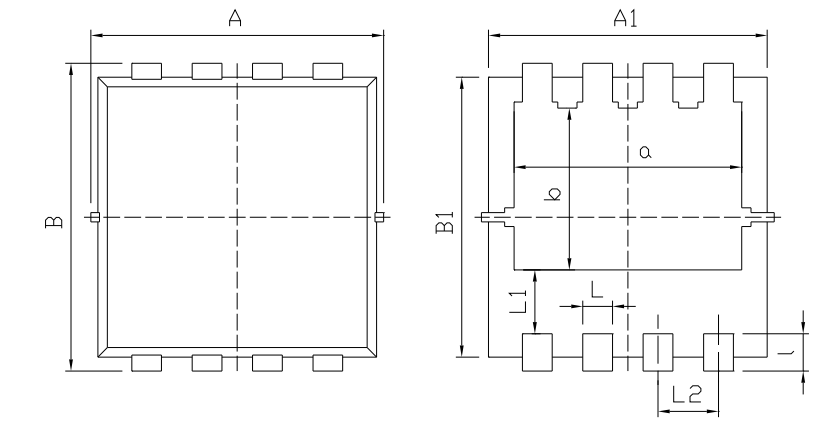




/ Package Dimensions

PDFN3X3A-8L

Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	3.20	3.30	3.40
A1	3.10	3.15	3.20
B	3.20	3.30	3.40
B1	2.95	3.00	3.05
C	0.75	0.80	0.85
L	0.25	0.30	0.35
L1	-	-	0.75
L2	0.55	0.65	0.75
L4	0.14	0.15	0.20
a	2.35	2.45	2.55
b	1.635	1.735	1.835
k	0.00	-	0.05
l	0.30	0.40	0.50

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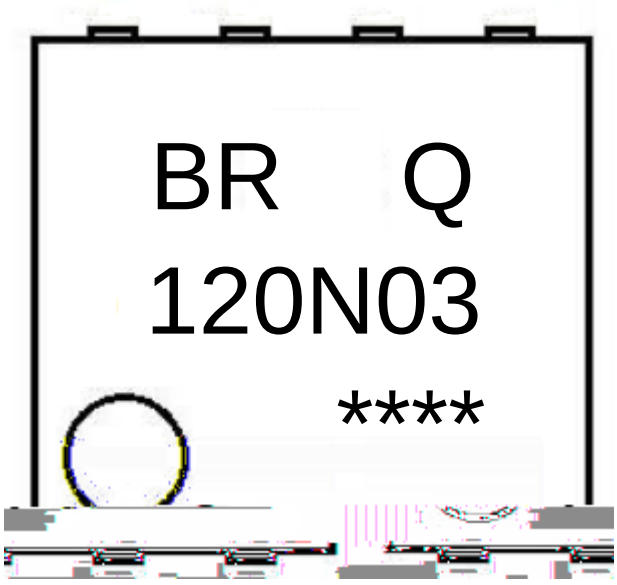
/ Marking Instructions



ب ˝ χ	
BR χ	⌘ ⅋ ᴵᴵ ⌐
Q χ	⌘ ∩ ⌐ ⍞ ƒ ᵝ ‰ ⅄
120N03 χ	⌘ ⅋ ᴺ ⌐
---- χ	⌘ ⊣ ƒ ᴵ ᴺ ⌐ ⊣ ⍟ ⊣ ƒ ᴵ ᴺ ᴾ ⍴

Note:

BR:	Company Code
Q:	Automobile halogen-free product Code
120N03:	Product Type Code
****:	Lot No. Code, code change with Lot No

( ) /

ب ˝ χ

1 أ ♬ □ ỷ 150 Ḱ 200 ɬ ı `H ڑ 60 Ḱ 120sec;

2 Š Ö □ ỷ 255 ° 5 ɬ ı `H ڑ ˙Y ⺈ ⺾ 5 ° 0.5sec;

3 ì ˙ ⺈ ˛ ɔ ھ ỷ ⺾ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:150~200 ɬ , Time:60~120sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

605 ° 5 ɬ